

EO-532-N/0.2~0.8mJ

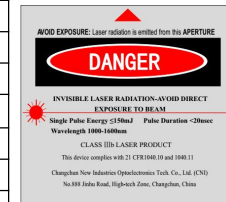
HIGH ENERGY DIODE PUMPED ALL-SOLID-STATE Q-SWITCHED LASER

High energy diode pumped all solid state Q-switched laser at 532nm has the features of high single pulse energy, short pulse duration, and high peak power, which is widely used in topography measurement, marking, ranging, glass carving, micro-processing, scientific research, and so on.

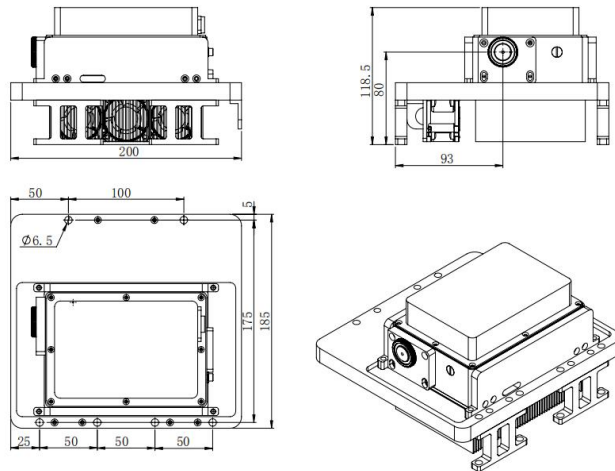


SPECIFICATIONS

Wavelength (nm)	532±1			
Operating mode	Q-switched: EO (Electro-optic)			
Single pulse energy (mJ)	0.4@1KHz	0.4@5KHz	0.2@20KHz	0.8@3KHz
Pulse duration (ns)	<6@1KHz	<6@5KHz	<7@20KHz	<11@3KHz
Rep. rate (Hz)	1Hz~1kHz	1k~7kHz	1k~25kHz	One fixed value between 1k~3kHz
Power stability (rms)	<1%, <2%			
M ²	<1.5		<2	
Pointing stability (urad, std)	<20			
Beam divergence, full angle (mrad)	<3			
Beam diameter (mm)	~1			
Beam height from base plate (mm)	80			
Warm-up time (minutes)	<15			
Cooled method	Air cooled			
Operating temperature (°C)	15~30			
Power supply (DC 24V)	PSU-EO-N			
Expected lifetime (hours)	10000			
Warranty period	1 year			
Options	Higher energy can be customized; Higher frequency can be customized			

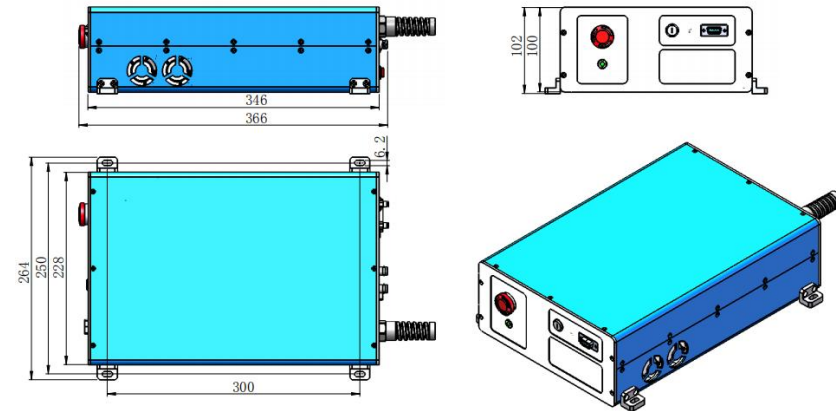


EO-532-N



200(L)×185(W)×118.5(H)mm³ 5.7kg

PSU-EO-N(DC 24V)



366(L)×264(W)×102(H)mm³ 6.5kg